

SANYO	No.3761A	2SJ188
P-Channel MOS Silicon FET		
Very High-Speed Switching Applications		

Features

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

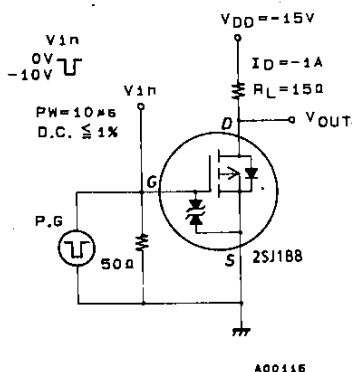
Absolute Maximum Ratings at Ta = 25°C

Drain to Source Voltage	V_{DSS}	-30	unit V
Gate to Source Voltage	V_{GSS}	±15	V
Drain Current (DC)	I_D	-2	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10 \mu s, \text{ duty cycle} \leq 1\%$	-8 A
Allowable Power Dissipation	P_D	$T_c = 25^\circ C$	20 W
Channel Temperature	T_{ch}	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

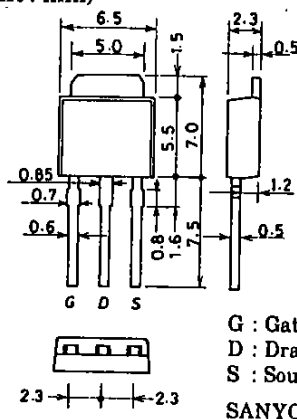
Electrical Characteristics at Ta = 25°C

			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-30			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100 \mu A, V_{DS} = 0$	±15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -1A$	1.2	2		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -1A, V_{GS} = -10V$		0.2	0.3	Ω
	$R_{DS(on)}$	$I_D = -1A, V_{GS} = -4V$		0.3	0.45	Ω
Input Capacitance	C_{iss}	$V_{DS} = -10V, f = 1MHz$		400		pF
Output Capacitance	C_{oss}	$V_{DS} = -10V, f = 1MHz$		280		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10V, f = 1MHz$		110		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		12		ns
Rise Time	t_r	∥		25		ns
Turn-OFF Delay Time	$t_{d(off)}$	∥		105		ns
Fall Time	t_f	∥		75		ns
Diode Forward Voltage	V_{SD}	$I_S = -2A, V_{GS} = 0$	-1.0		-1.5	V

Switching Time Test Circuit

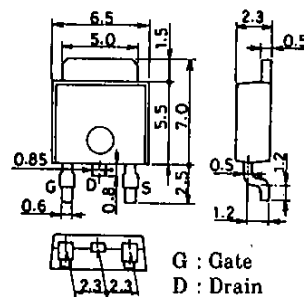


Package Dimensions 2083A (unit: mm)



G : Gate
D : Drain
S : Source
SANYO : TP

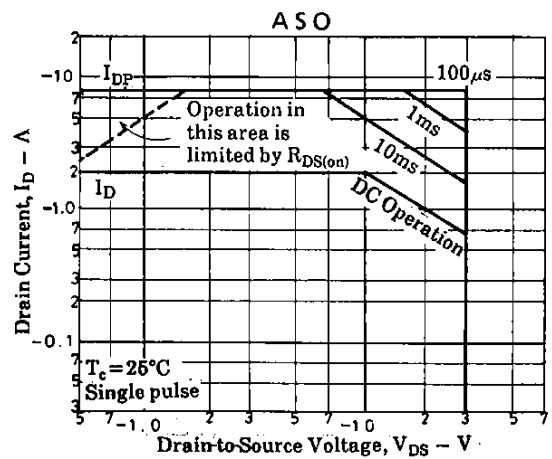
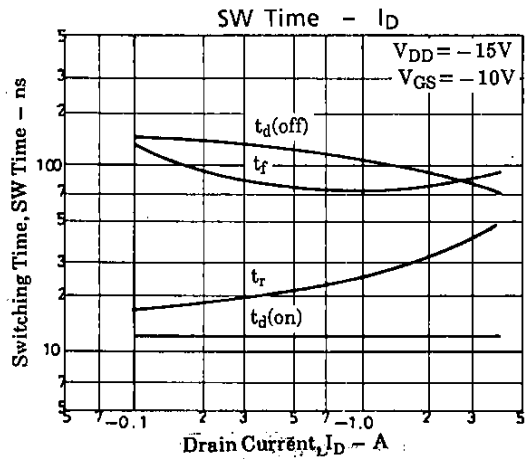
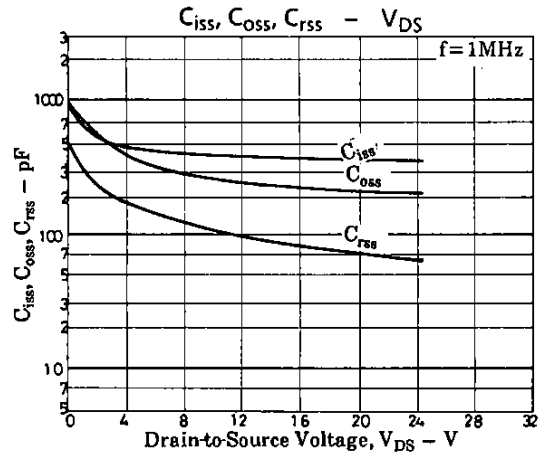
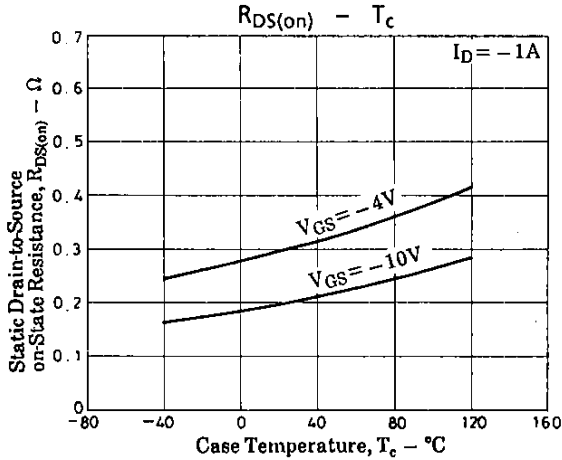
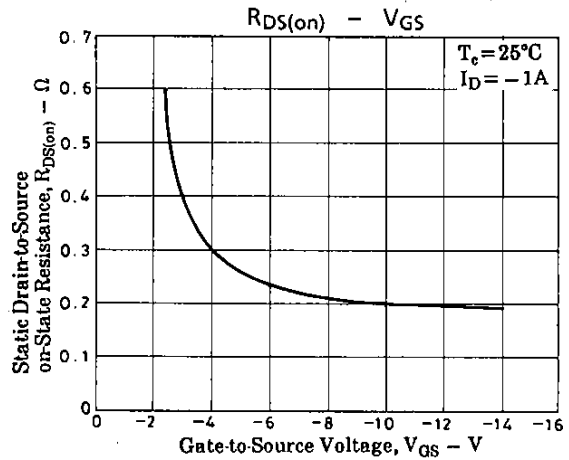
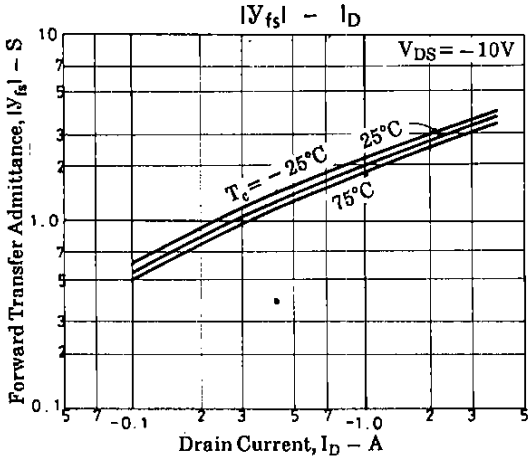
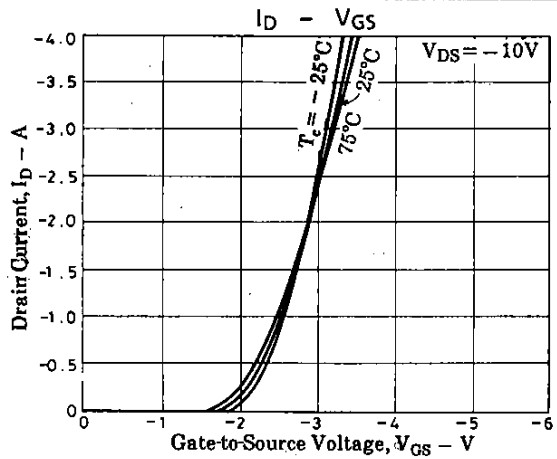
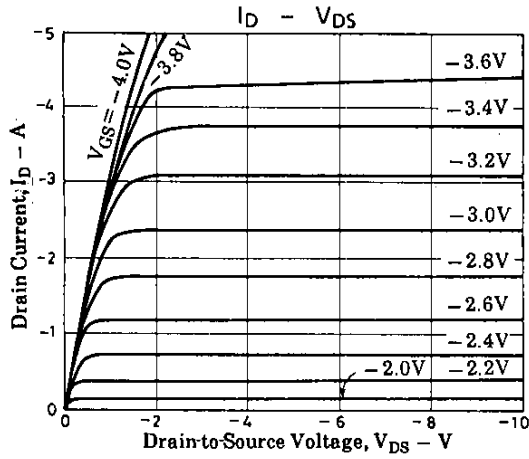
Package Dimensions 2092A (unit: mm)

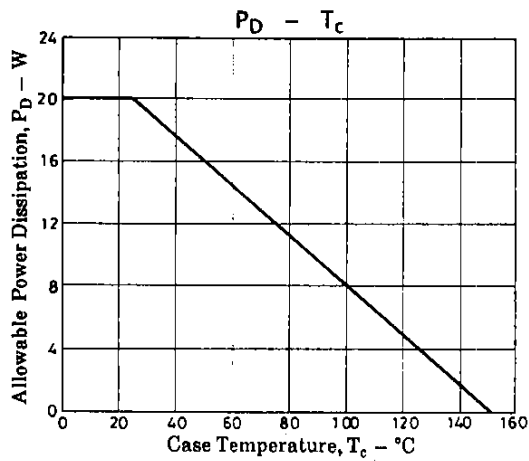


G : Gate
D : Drain
S : Source
SANYO : TP-FA

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

42893TH/N1292MH (KOTO) 8-7308, 7921 No.3761-1/3





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